

BUK7610-100B

N-channel TrenchMOS standard level FET

6 July 2012

Product data sheet

1. Product profile

1.1 General description

Standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

1.2 Features and benefits

- Low conduction losses due to low on-state resistance
- Q101 compliant
- Suitable for standard level gate drive sources
- Suitable for thermally demanding environments due to 175 °C rating

1.3 Applications

- 12 V, 24 V and 42 V loads
- Automotive systems
- General purpose power switching
- Motors, lamps and solenoids

1.4 Quick reference data

Table 1. Quick reference data

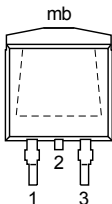
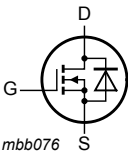
Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25\text{ °C}$; $T_j \leq 175\text{ °C}$		-	-	100	V
I_D	drain current	$V_{GS} = 10\text{ V}$; $T_{mb} = 25\text{ °C}$; Fig. 1 ; Fig. 3	[1]	-	-	75	A
P_{tot}	total power dissipation	$T_{mb} = 25\text{ °C}$; Fig. 2		-	-	300	W
Static characteristics							
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10\text{ V}$; $I_D = 25\text{ A}$; $T_j = 25\text{ °C}$; Fig. 11 ; Fig. 12		-	8.6	10	mΩ
Dynamic characteristics							
Q_{GD}	gate-drain charge	$V_{GS} = 10\text{ V}$; $I_D = 25\text{ A}$; $V_{DS} = 80\text{ V}$; $T_j = 25\text{ °C}$; Fig. 13		-	22	-	nC
Avalanche ruggedness							
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$I_D = 75\text{ A}$; $V_{sup} \leq 100\text{ V}$; $R_{GS} = 50\text{ Ω}$; $V_{GS} = 10\text{ V}$; $T_{j(init)} = 25\text{ °C}$; unclamped		-	-	629	mJ



[1] Continuous current is limited by package.

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	 D2PAK (SOT404)	 mbb076
2	D	drain[1]		
3	S	source		
mb	D	mounting base; connected to drain		

[1] It is not possible to make connection to pin 2.

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BUK7610-100B	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

4. Marking

Table 4. Marking codes

Type number	Marking code
BUK7610-100B	BUK7610-100B

5. Limiting values

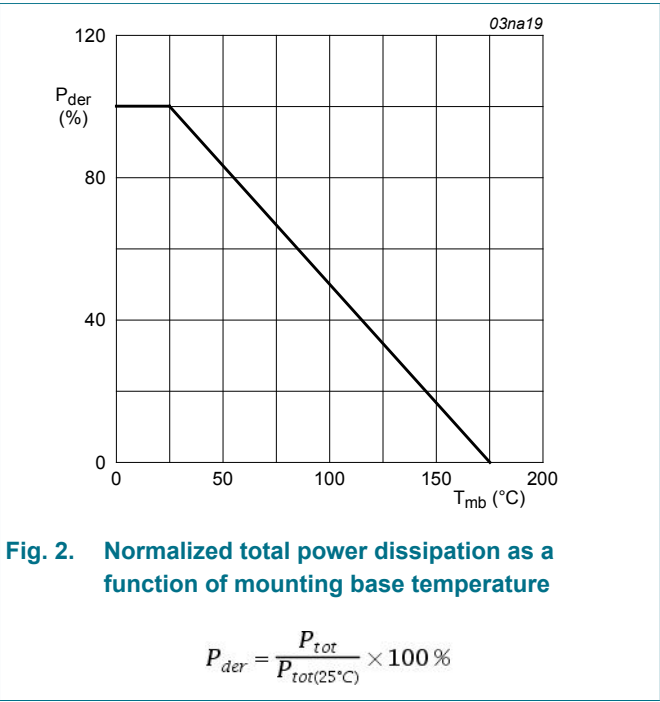
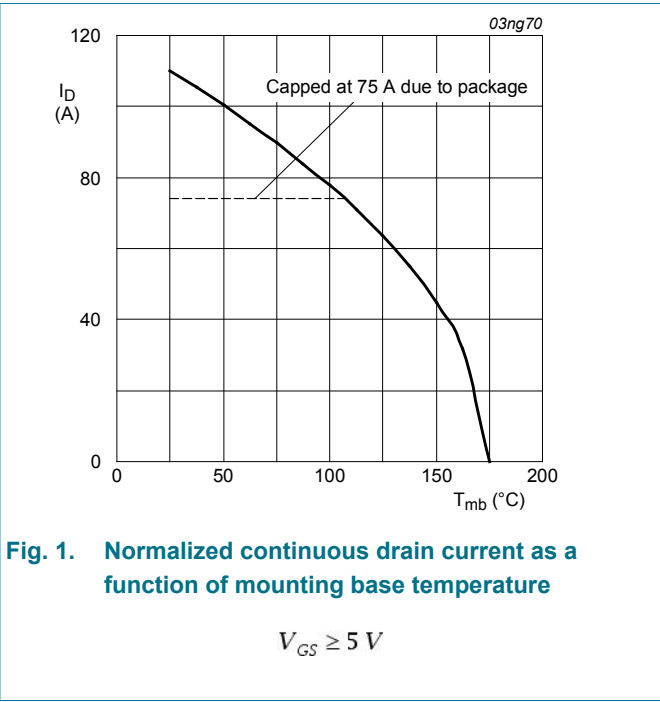
Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25\text{ °C}$; $T_j \leq 175\text{ °C}$		-	100	V
V_{DGR}	drain-gate voltage	$R_{GS} = 20\text{ k}\Omega$		-	100	V
V_{GS}	gate-source voltage			-20	20	V
I_D	drain current	$T_{mb} = 25\text{ °C}$; $V_{GS} = 10\text{ V}$; Fig. 1; Fig. 3	[1]	-	110	A
			[2]	-	75	A
		$T_{mb} = 100\text{ °C}$; $V_{GS} = 10\text{ V}$; Fig. 1	[2]	-	75	A
I_{DM}	peak drain current	$T_{mb} = 25\text{ °C}$; pulsed; $t_p \leq 10\text{ }\mu\text{s}$; Fig. 3		-	438	A

Symbol	Parameter	Conditions		Min	Max	Unit
P _{tot}	total power dissipation	T _{mb} = 25 °C; Fig. 2		-	300	W
T _{stg}	storage temperature			-55	175	°C
T _j	junction temperature			-55	175	°C
Source-drain diode						
I _S	source current	T _{mb} = 25 °C	[1]	-	110	A
			[2]	-	75	A
I _{SM}	peak source current	pulsed; t _p ≤ 10 μs; T _{mb} = 25 °C		-	438	A
Avalanche ruggedness						
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	I _D = 75 A; V _{sup} ≤ 100 V; R _{GS} = 50 Ω; V _{GS} = 10 V; T _{j(init)} = 25 °C; unclamped		-	629	mJ

- [1] Current is limited by power dissipation chip rating.
- [2] Continuous current is limited by package.



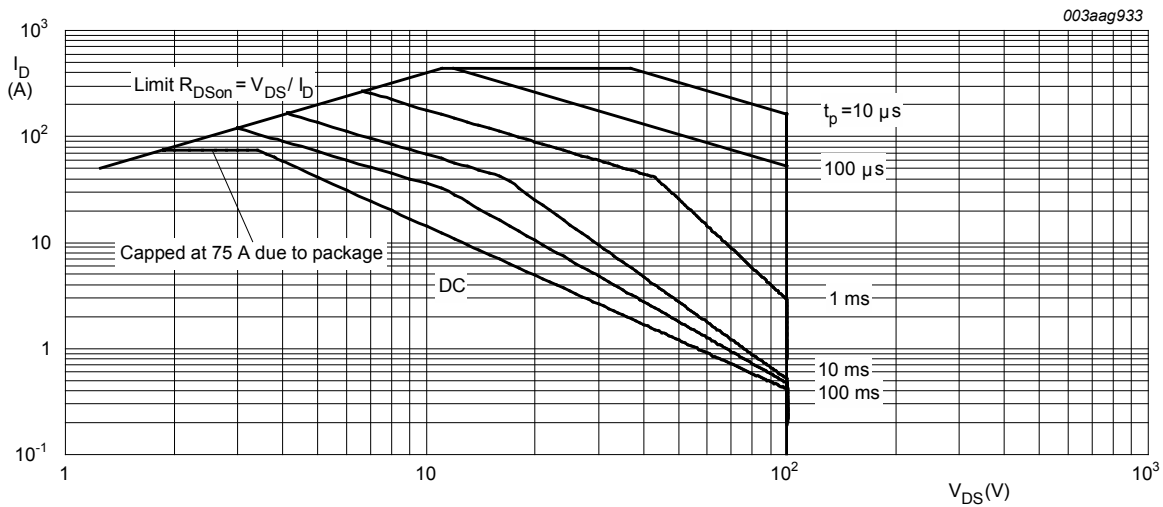


Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

$T_{mb} = 25^{\circ}C$; I_{DM} is a single pulse

6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	Fig. 4	-	-	0.5	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	mounted on printed-circuit board ; minimum footprint	-	50	-	K/W

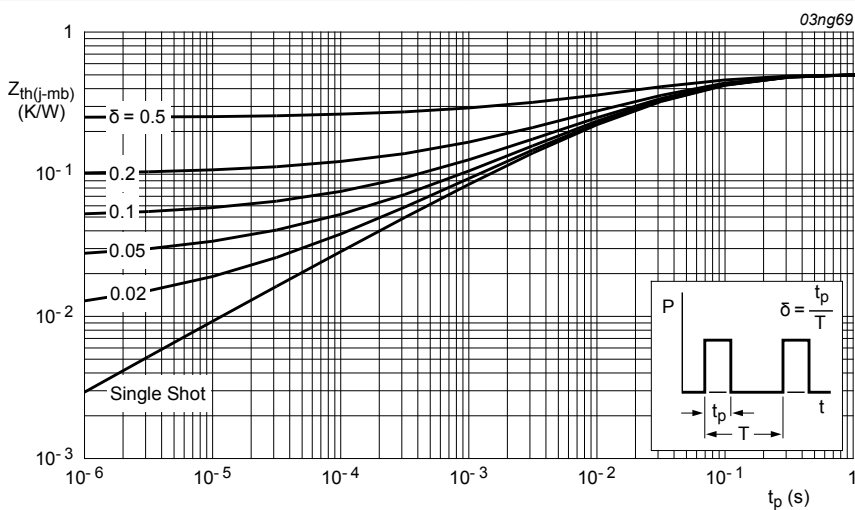


Fig. 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

7. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Static characteristics							
V _{(BR)DSS}	drain-source breakdown voltage	I _D = 0.25 mA; V _{GS} = 0 V; T _j = 25 °C		100	-	-	V
		I _D = 0.25 mA; V _{GS} = 0 V; T _j = -55 °C		89	-	-	V
V _{GS(th)}	gate-source threshold voltage	I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 175 °C; Fig. 10		1	-	-	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 25 °C; Fig. 10		2	3	4	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _j = -55 °C; Fig. 10		-	-	4.4	V
I _{DSS}	drain leakage current	V _{DS} = 100 V; V _{GS} = 0 V; T _j = 25 °C		-	0.02	1	μA
		V _{DS} = 100 V; V _{GS} = 0 V; T _j = 175 °C		-	-	500	μA
I _{GSS}	gate leakage current	V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C		-	2	100	nA
		V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C		-	2	100	nA
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; Fig. 11; Fig. 12		-	8.6	10	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 175 °C; Fig. 11; Fig. 12		-	-	25	mΩ
Dynamic characteristics							
Q _{G(tot)}	total gate charge	I _D = 25 A; V _{DS} = 80 V; V _{GS} = 10 V; T _j = 25 °C; Fig. 13		-	80	-	nC
Q _{GS}	gate-source charge			-	18	-	nC
Q _{GD}	gate-drain charge			-	22	-	nC
C _{iss}	input capacitance	V _{GS} = 0 V; V _{DS} = 25 V; f = 1 MHz; T _j = 25 °C; Fig. 14		-	5080	6773	pF
C _{oss}	output capacitance			-	677	812	pF
C _{rss}	reverse transfer capacitance			-	168	230	pF
t _{d(on)}	turn-on delay time	V _{DS} = 30 V; R _L = 1.2 Ω; V _{GS} = 10 V; R _{G(ext)} = 10 Ω; T _j = 25 °C		-	33	-	ns
t _r	rise time			-	45	-	ns
t _{d(off)}	turn-off delay time			-	120	-	ns
t _f	fall time			-	36	-	ns
L _D	internal drain inductance	from drain lead 6 mm from package to centre of die ; T _j = 25 °C		-	4.5	-	nH
		from upper edge of drain mounting base to centre of die ; T _j = 25 °C		-	2.5	-	nH
L _S	internal source inductance	from source lead to source bond pad ; T _j = 25 °C		-	7.5	-	nH

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Source-drain diode						
V_{SD}	source-drain voltage	$I_S = 40\text{ A}$; $V_{GS} = 0\text{ V}$; $T_J = 25\text{ }^{\circ}\text{C}$; Fig. 15	-	0.85	1.2	V
t_{rr}	reverse recovery time	$I_S = 20\text{ A}$; $dI_S/dt = -100\text{ A}/\mu\text{s}$;	-	69	-	ns
Q_r	recovered charge	$V_{GS} = -10\text{ V}$; $V_{DS} = 30\text{ V}$; $T_J = 25\text{ }^{\circ}\text{C}$	-	212	-	nC

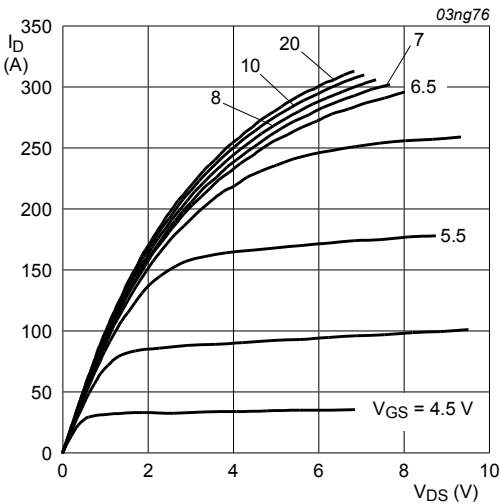


Fig. 5. Output characteristics: drain current as a function of drain-source voltage; typical values

$T_J = 25\text{ }^{\circ}\text{C}; t_p = 300\mu\text{s}$

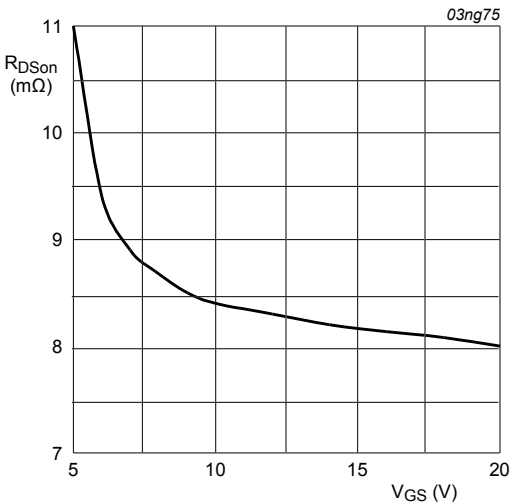


Fig. 6. Drain-source on-state resistance as a function of gate-source voltage; typical values

$T_J = 25\text{ }^{\circ}\text{C}; I_D = 25\text{ A}$

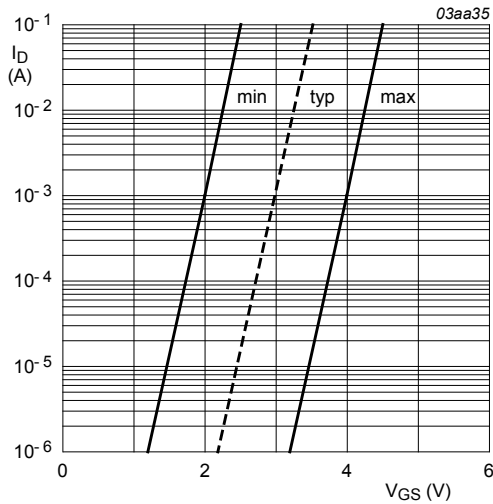


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

$T_J = 25\text{ }^{\circ}\text{C}; V_{DS} = 5\text{ V}$

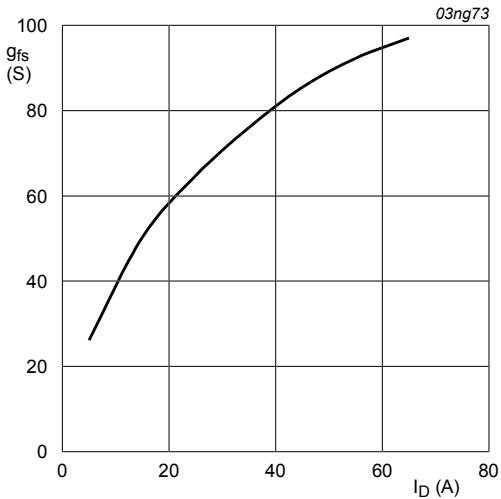


Fig. 8. Forward transconductance as a function of drain current; typical values

$T_J = 25\text{ }^{\circ}\text{C}; V_{DS} = 25\text{ V}$

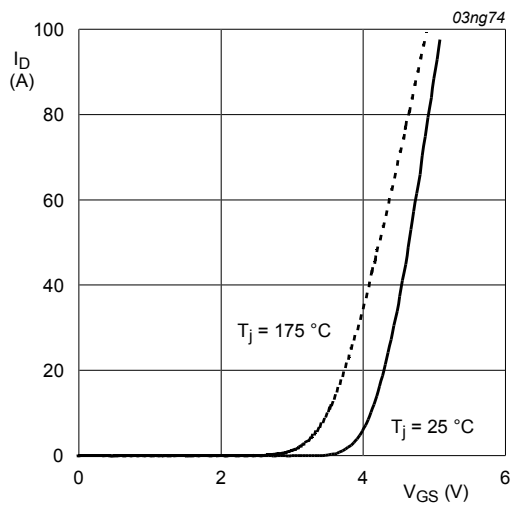


Fig. 9. Transfer characteristics: drain current as a function of gate-source voltage; typical values

$$V_{DS} = 25\text{V}$$

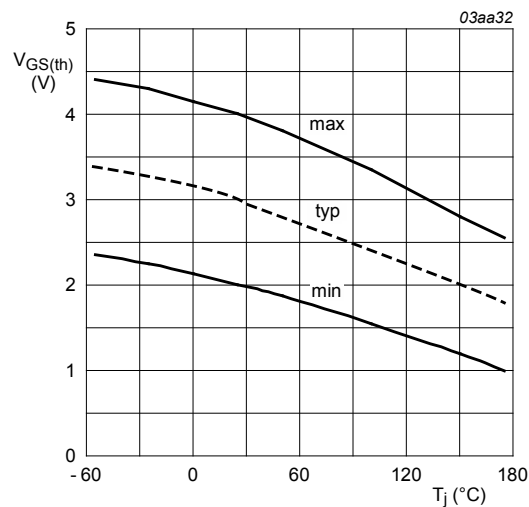


Fig. 10. Gate-source threshold voltage as a function of junction temperature

$$I_D = 1\text{mA}; V_{DS} = V_{GS}$$

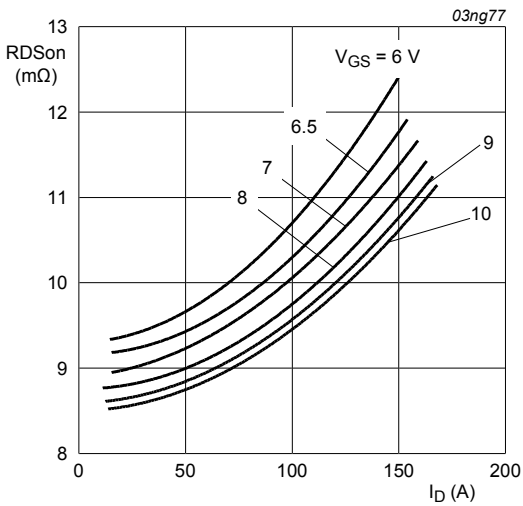


Fig. 11. Drain-source on-state resistance as a function of drain current; typical values

$$T_j = 25\text{ }^\circ\text{C}$$

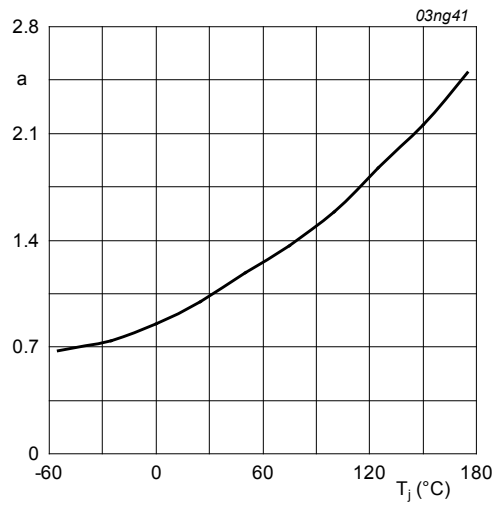


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon(25\text{ }^\circ\text{C})}}$$

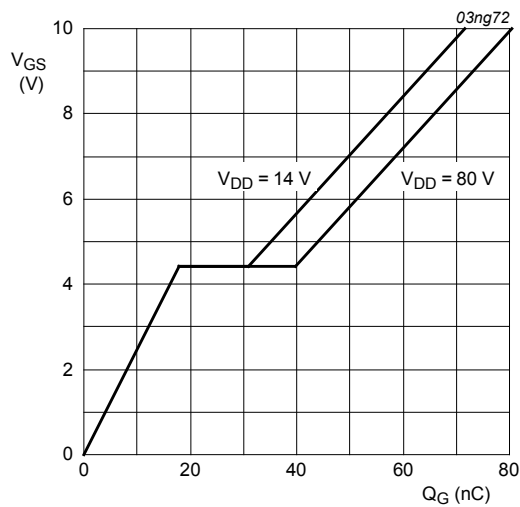


Fig. 13. Gate-source voltage as a function of gate charge; typical values

$T_j = 25^\circ\text{C}; I_D = 25\text{ A}$

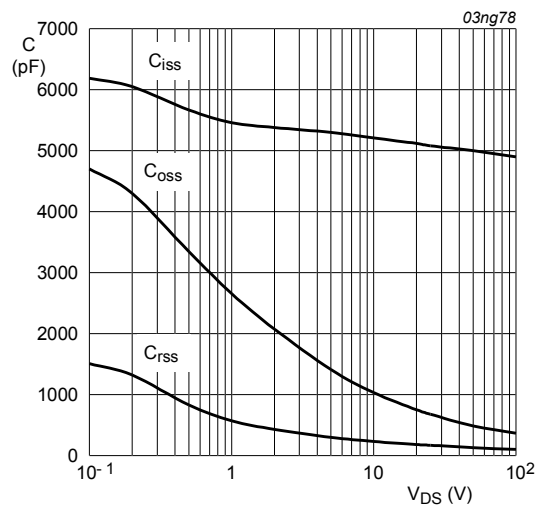


Fig. 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$V_{GS} = 0\text{ V}; f = 1\text{ MHz}$

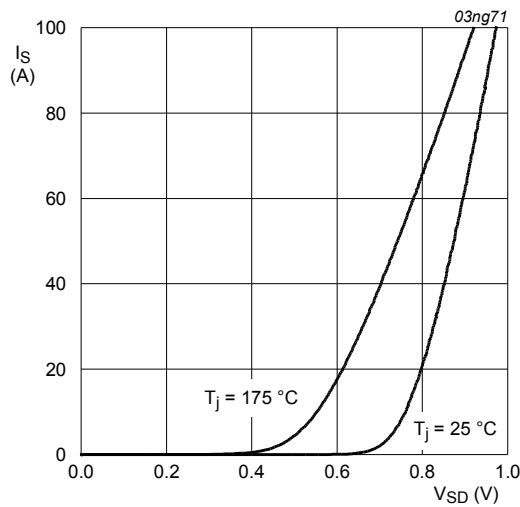


Fig. 15. Reverse diode current as a function of reverse diode voltage; typical value

$V_{GS} = 0\text{ V}$

8. Package outline

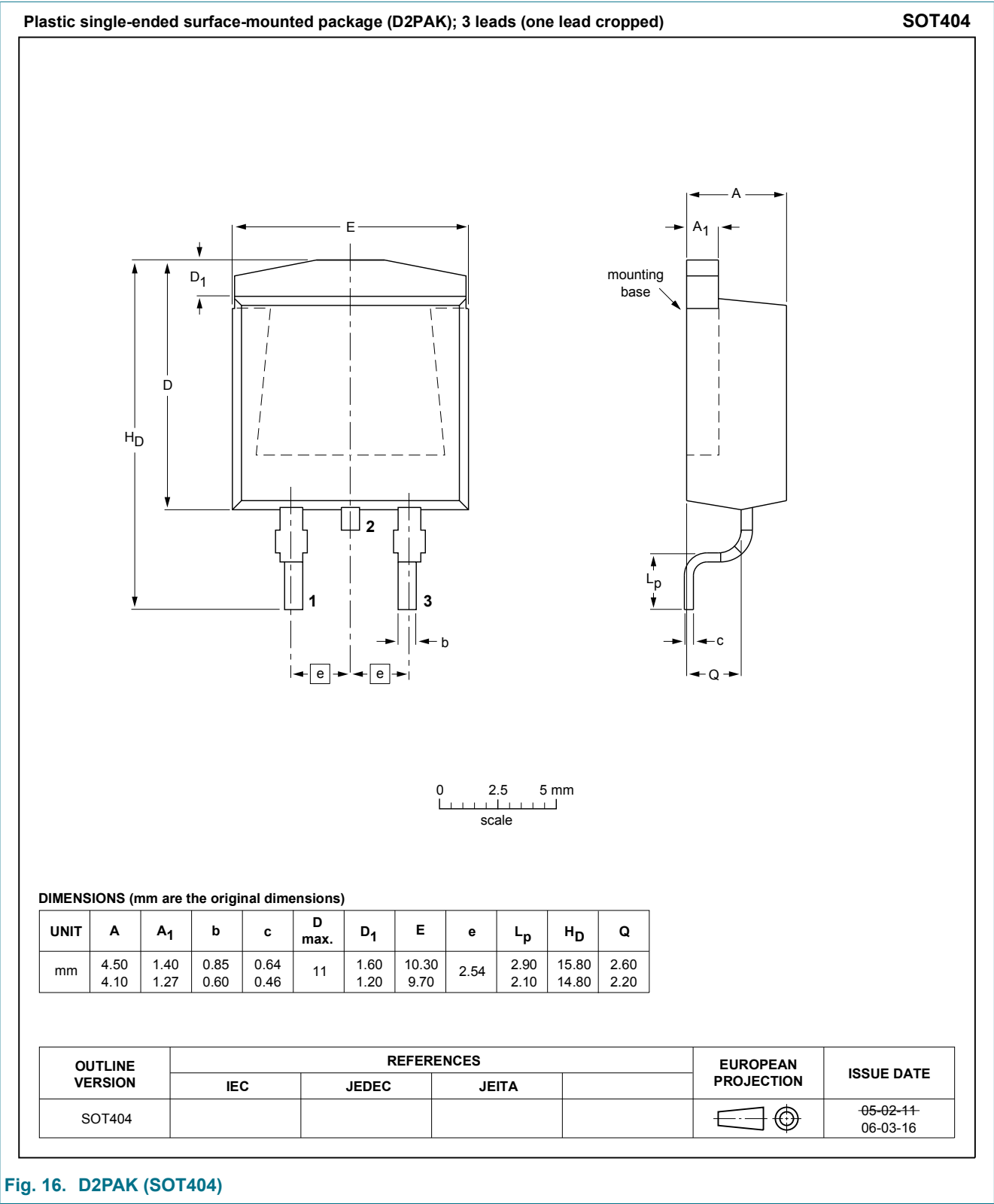


Fig. 16. D2PAK (SOT404)

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Document status [1][2]	Product status [3]	Definition
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